

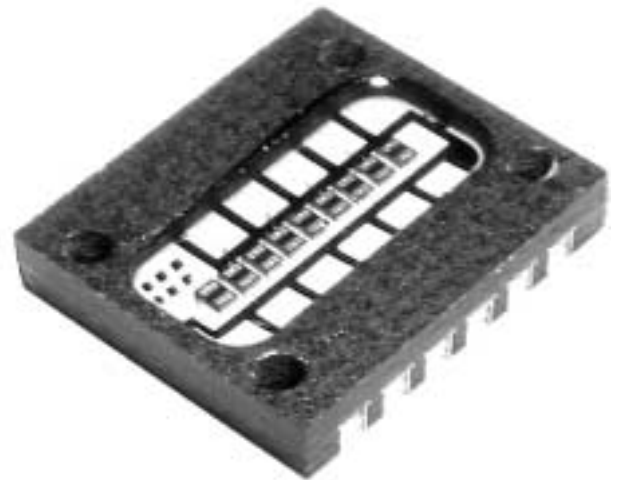
9-Element SMD Phototransistor Array

Features

- High speed phototransistor OL8110 chips
- Reference holes for precise mounting
- Compact size and low cost
- Also available with mounted reticle
- Custom design available
- Single chip placement for high speed applications

Application

- Optical Encoders (absolute, incremental, multi turn)
- Edge detection for paper
- Multi Element Sensor Array



Absolute Maximum Ratings

Storage and Operating Temperature	-35 to +85 °C (*)
Solder Temperature (Vapor Phase Reflow for 30 sec)	235 °C

(*)Military Temperature range available on request

Electrical Specifications ($T_A = 25^\circ\text{C}$)

- Parameters 100% tested at waferprobe

Parameter	Units	Min	Typ	Max
I_{CE0} @ 52.0 V	μA		0.1	100.0
I_{DARK} @ 32.0 V	nA		1.0	100.0
I_{EC0} @ 7.7 V	μA		0.1	100.0
V_{CESt} ($I_C = 2.0$ mA, $I_B = 22.2$ μA)	mV		290.0	400.0
HFE ($I_C = 2.0$ mA, $V_{CE} = 5.0$ V)		500.0	750.0	1000.0

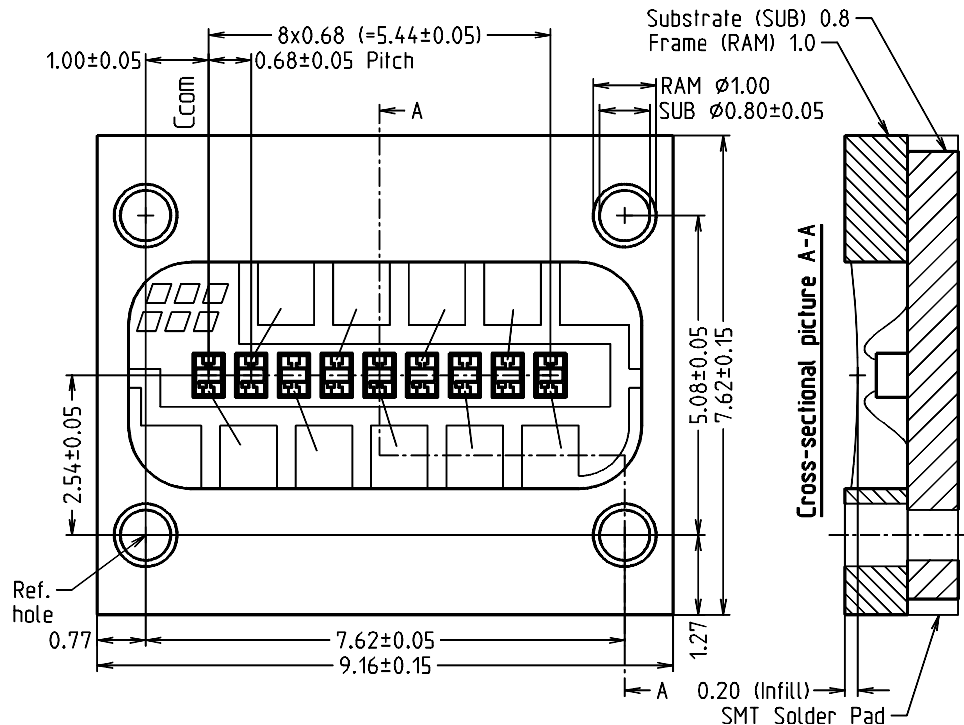
Additional Parameters tested for qualification and on a lot sample basis

- Rise time: 10.0 μs ($V_{CC} = 5.0$ V, $R_L = 1.2$ k Ω , $C_L = 8.0$ pF, $V_E(\text{peak}) = 1.0$ V)
- Fall time: 13.0 μs ($V_{CC} = 5.0$ V, $R_L = 1.2$ k Ω , $C_L = 8.0$ pF, $V_E(\text{peak}) = 1.0$ V)
- Responsivity peak wavelength: 880 nm

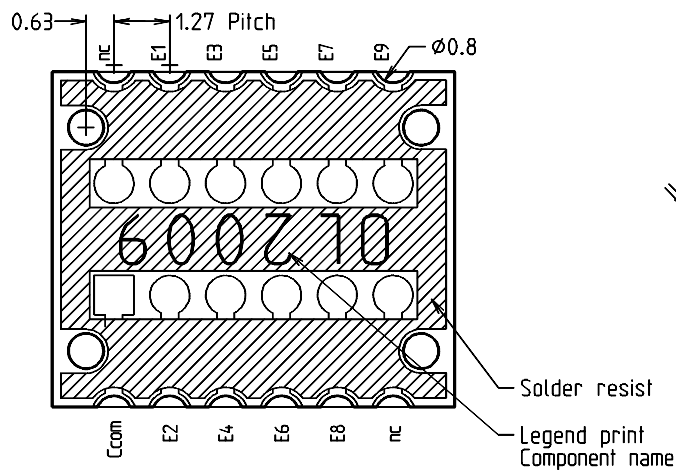
Note

Please see part **ET8001**, precision schmitt trigger and comparator array with hysteresis tracking function for use with this phototransistor array.

Top view



Bottom view



Chip type:
OL8110 (9x) Phototransistor
Chip thickness: 178 μ m - 254 μ m

